

MOSFET

Comchip

SMD Diode Specialist

CJ3139KDW-G (Dual P-Channel)

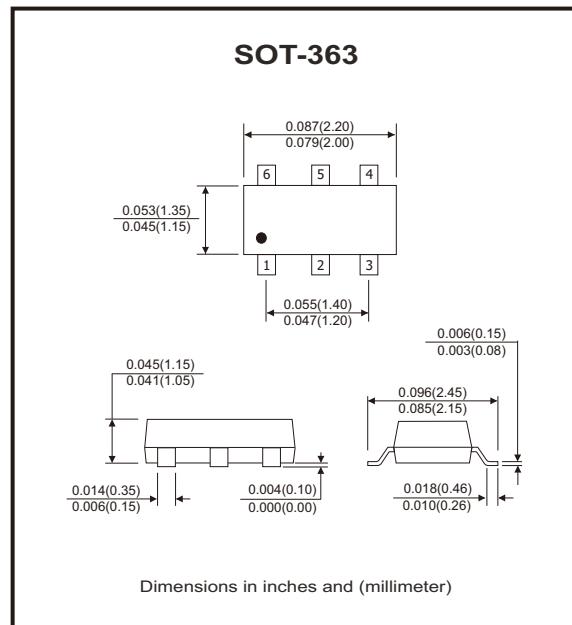
RoHS Device



V(BR)DSS	RDS(on)MAX	ID
-20V	520mΩ @ -4.5V	-0.66A
	700mΩ @ -2.5V	
	950mΩ(TYP) @ -1.8V	

Features

- High-side switching.
 - Low on-resistance.
 - Low threshold.
 - Fast switching speed

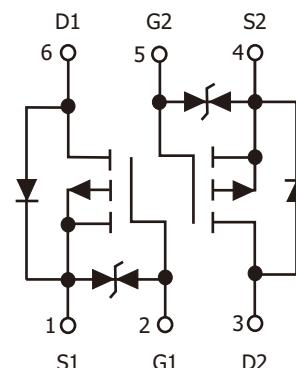


Mechanical data

- Case: SOT-363, molded plastic.
 - Terminals: Solderable per MIL-STD-750,
method 2026.
 - Weight: 0.006 grams (approx.).

Circuit Diagram

G : Gate
S : Source
D : Drain



Maximum Ratings (at Ta=25 °C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	V _{DSS}	-20	V
Typ. Gate-source voltage	V _{Gs}	±12	V
Drain current-continuous	I _{D(DC)}	-0.66	A
Drain current-pulsed (Note 1)	I _{DM(pulse)}	-2.64	A
Power dissipation (Note 2)	P _D	150	mW
Thermal resistance from junction to ambient	R _{θJA}	833	°C/W
Junction temperature range	T _J	-40 to +150	°C
Storage temperature range	T _{STG}	-55 to +150	°C

Electrical Characteristics (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
On/Off States						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	-20			V
Gate threshold voltage (Note 3)	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-0.35		-1.1	V
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 10\text{V}, V_{DS} = 0\text{V}$			± 20	μA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$			-1	μA
Drain-source on-state resistance (Note 3)	$R_{DS(\text{on})}$	$V_{GS} = -4.5\text{V}, I_D = -1\text{AA}$			520	$\text{m}\Omega$
		$V_{GS} = -2.5\text{V}, I_D = -800\text{mA}$			700	
		$V_{GS} = -1.8\text{V}, I_D = -500\text{mA}$		950		
Forward transconductance	g_{fs}	$V_{DS} = -10\text{V}, I_D = -540\text{mA}$	0.8			S
Dynamic characteristics (Note 4)						
Input capacitance	C_{iss}	$V_{DS} = -16\text{V}, V_{GS} = 0\text{V}$ $f = 1\text{MHz}$			170	pF
Output capacitance	C_{oss}				25	
Reverse transfer capacitance	C_{rss}				15	
Switching time (Note 4)						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -10\text{V}, I_D = -200\text{mA}$ $V_{GS} = -4.5\text{V}, R_G = 10\Omega$		9		nS
Rise time	t_r			5.8		
Turn-off delay time	$t_{d(off)}$			32.7		
Fall time	t_f			20.3		
Drain-source diode characteristics						
Drain-source diode forward voltage (Note 3)	V_{SD}	$I_S = -0.5\text{A}, V_{GS} = 0\text{V}$			-1.2	V

Notes: 1. Repetitive rating: Pulse width limited by maximum junction temperature.

2. This test is performed with no heat sink at $T_A=25^\circ\text{C}$.

3. Pulse test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 0.5\%$.

4. These parameters have no way to verify.

Rating and Characteristic Curves (CJ3139KDW-G)

Fig.1 - Output Characteristics

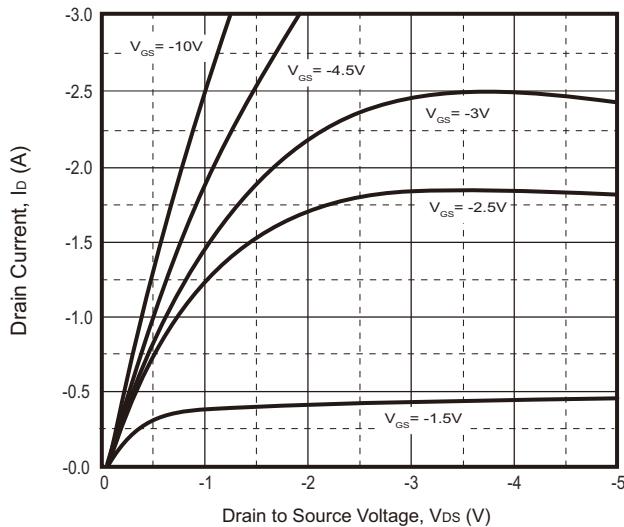


Fig.2 - Transfer Characteristics

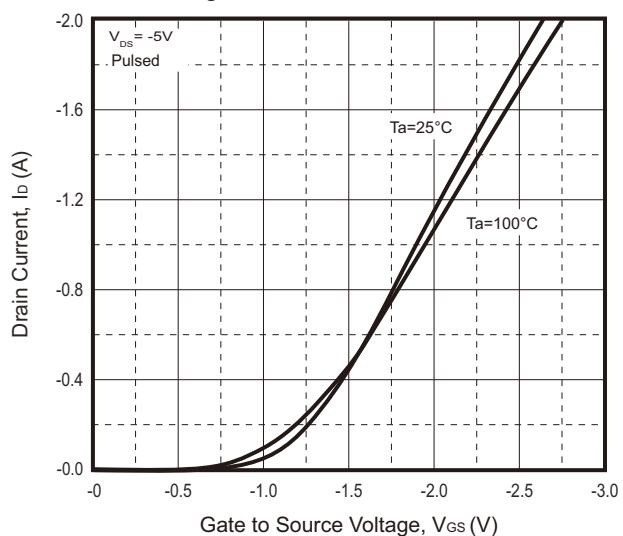


Fig.3 - $R_{DS(ON)}$ — I_D

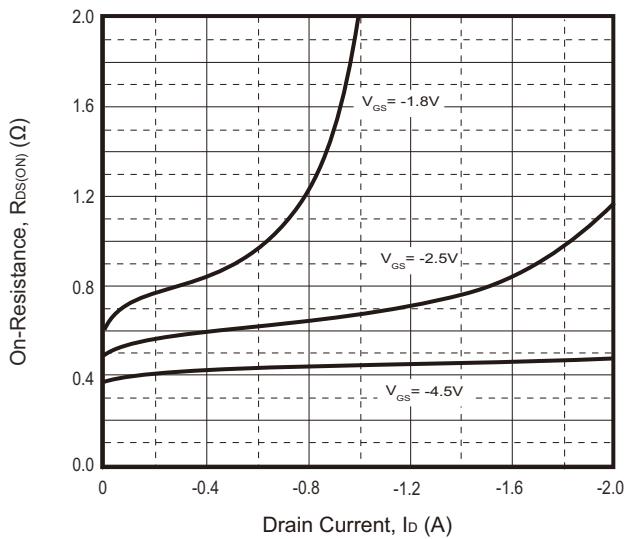


Fig.4 - $R_{DS(ON)}$ — V_{GS}

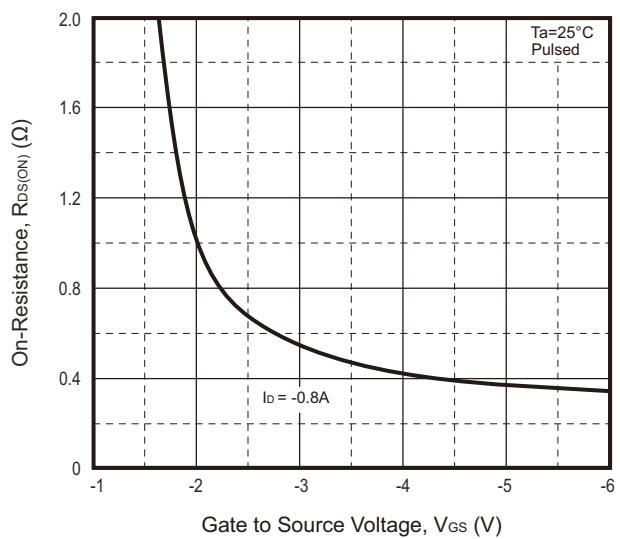


Fig.5 - I_S — V_{SD}

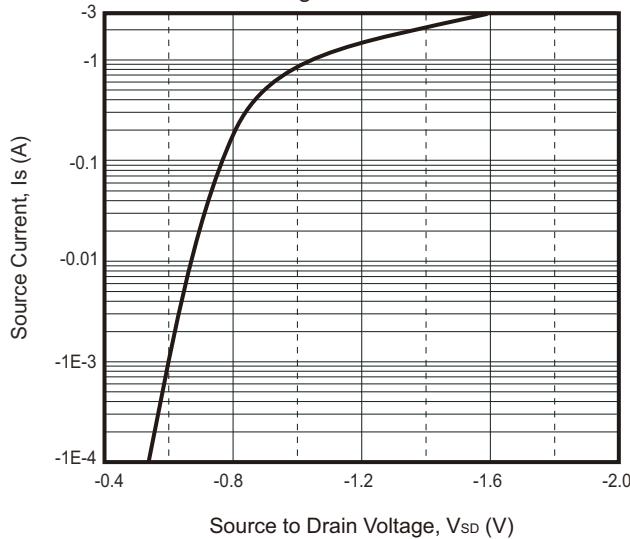
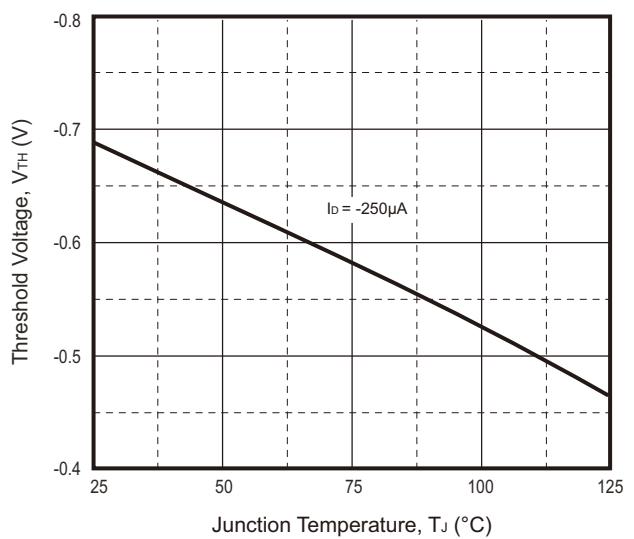


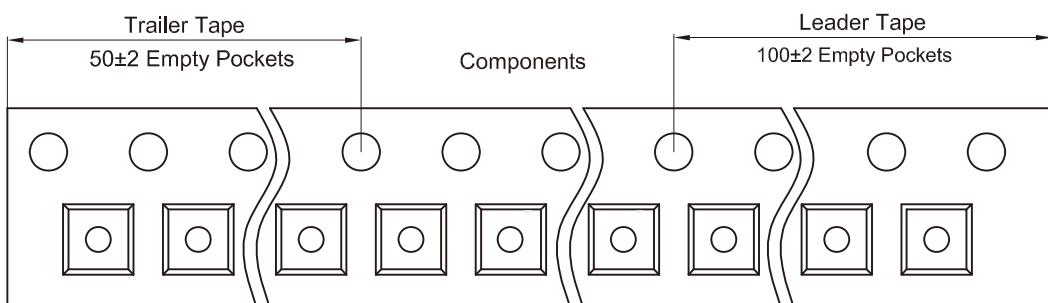
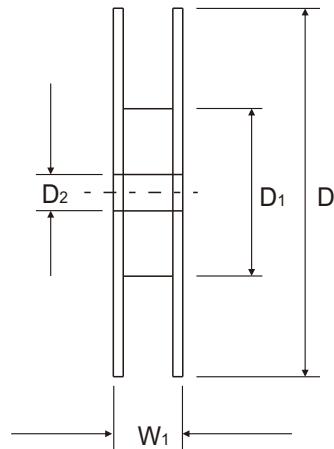
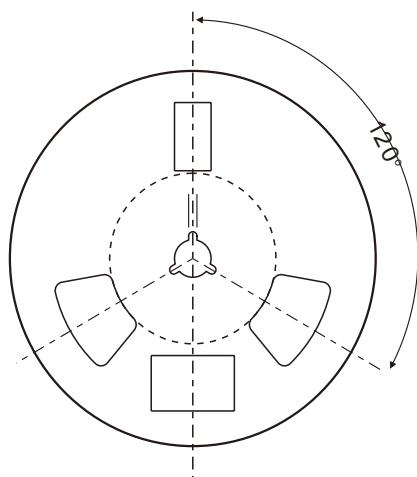
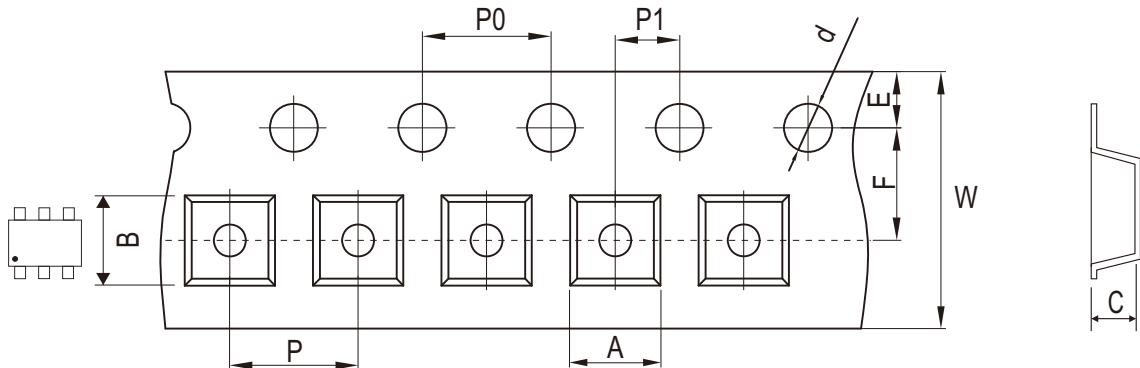
Fig.6 - Threshold Voltage



Company reserves the right to improve product design , functions and reliability without notice.

REV:B

Reel Taping Specification

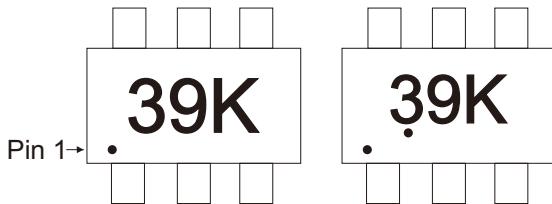


SOT-363	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	2.25 ± 0.05	2.55 ± 0.05	1.20 ± 0.05	1.50 ± 0.10	178.00 ± 2.00	54.40 ± 1.00	13.00 ± 1.00
	(inch)	0.089 ± 0.002	0.100 ± 0.002	0.047 ± 0.002	0.059 ± 0.004	7.008 ± 0.079	2.142 ± 0.039	0.512 ± 0.039

SOT-363	SYMBOL	E	F	P	P0	P1	W	W1
	(mm)	1.75 ± 0.10	3.50 ± 0.10	4.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.10	$8.00 + 0.30/-0.10$	12.30 ± 1.00
	(inch)	0.069 ± 0.004	0.138 ± 0.004	0.157 ± 0.004	0.157 ± 0.004	0.079 ± 0.004	$0.315 + 0.012/-0.004$	0.484 ± 0.039

Marking Code

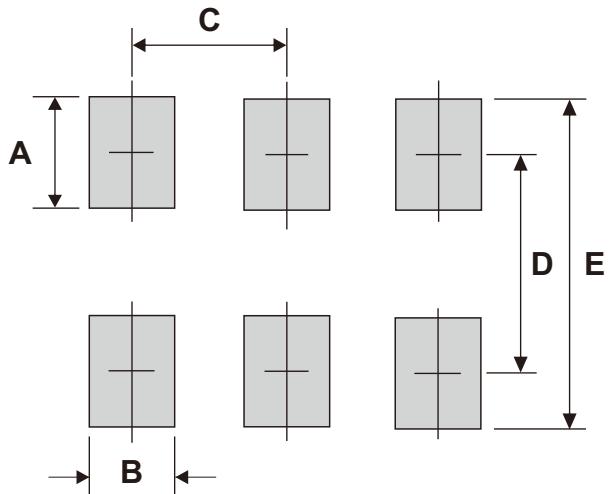
Part Number	Marking Code
CJ3139KDW-G	39K



Solid dot = Control code

Suggested P.C.B. PAD Layout

SIZE	SOT-363	
	(mm)	(inch)
A	0.80	0.032
B	0.40	0.016
C	0.65	0.026
D	1.94	0.076
E	2.74	0.108



Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
SOT-363	3,000	7